

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	09/945,554
	Filing Date	August 30, 2001
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2826
	Examiner Name	Dickey, Thomas
Sheet 1 of 1		Attorney Docket No: 1303.028US1

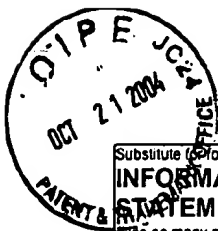
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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T ²
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EXAMINER

DATE CONSIDERED



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Substitute Disclosure Statement Form (PTO-1449)

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